Application No.: 09/851,325 Amendment dated 08/15/03 Reply to Office Action of 05/15/03

Amendments to the Specification:

Please amend the paragraph beginning on page 13, line 15 as follows:

A switching device, i.e., a thin film transistor (TFT), that is indicated by a portion "T", is positioned near the crossing of the gate and data lines 113 and 114. As shown in an enlarged view of a portion "T", gate and source electrodes 135 and 137 are positioned and electrically connected with the gate and data lines 113 and 115, respectively. A drain electrode 137 is spaced apart from the source electrode 135 and overlaps one end of the gate electrode 117. The source electrode 135 also overlaps the other end of the gate electrode 117. An active layer 133 is located over the gate electrode 117 and under the source and drain electrodes 135 and 137117. A first pixel-connecting line 145a, which is connected with respective first ends of pixel electrodes 145, electrically contacts the drain electrode 137 through a drain contact hole 139 and is disposed parallel with the gate line 113.